VS-HFA16TA60CS-M3

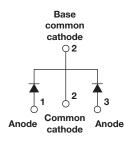
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 8 A



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D²PAK (TO-263AB)



PRIMARY CHARACTERISTICS					
I _{F(AV)}	2 x 8 A				
V _R	600 V				
V _F at I _F	1.4 V				
t _{rr} typ.	18 ns				
T _J max.	150 °C				
Package	D ² PAK (TO-263AB)				
Circuit configuration	Common cathode				

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA16TA60CS is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 8 A per leg continuous current, the VS-HFA16TA60CS is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA16TA60CS is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		600	V		
Maximum continuous forward currentper leg			T _C = 100 °C	8		
per device	IF	$1_{\rm C} = 100$ C	16	А		
Single pulse forward current	I _{FSM}		60	~		
Maximum repetitive forward current	I _{FRM}		24			
Maximum power dissipation	P _D	T _C = 25 °C	36	W		
		T _C = 100 °C	14	vv		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C		

Revision: 16-Dec-2021

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Document Number: 96220

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ELECTRICAL SPECIFICATIONS PER LEG ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS		
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-			
Maximum forward voltage		I _F = 8.0 A		-	1.4	1.7	v		
	V_{FM}	I _F = 16 A	See fig. 1	-	1.7	2.1			
		$I_F = 8.0 \text{ A}, T_J = 125 \text{ °C}$		-	1.4	1.7			
Maximum reverse leakage current		$V_{R} = V_{R}$ rated	See fig. 2	-	0.3	5.0	μA		
Maximum reverse leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	See lig. 2	-	100	500	μΑ		
Junction capacitance	CT	V _R = 200 V See fig. 3		-	10	25	pF		
Series inductance	L _S	Measured lead to lead 5 mm from pa	Measured lead to lead 5 mm from package body -			-	nH		

DYNAMIC RECOVERY CHARACTERISTICS PER LEG (T_J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
5	t _{rr}	I _F = 1.0 A, dI _F /dt = 200	A/µs, V _R = 30 V	-	18	-			
Reverse recovery time See fig. 5, 6 and 16	t _{rr1}	T _J = 25 °C		-	37	55	ns		
	t _{rr2}	T _J = 125 °C	I _F = 8.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	55	90			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	3.5	5.0	А		
See fig. 7 and 8	I _{RRM2}	T _J = 125 °C		-	4.5	8.0	A		
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	65	138	nC		
See fig. 9 and 10	Q _{rr2}	T _J = 125 °C		-	124	360	no		
Peak rate of fall of recovery current	dl _{(rec)M} /dt1	T _J = 25 °C		-	240	-	A /uo		
during t_b , see fig. 11 & 12	dl _{(rec)M} /dt2	T _J = 125 °C		-	210	-	A∕µs		

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER SYMBOL TEST CONDITIONS				TYP.	MAX.	UNITS	
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C	
Junction to case, single leg conducting			-	-	3.5		
Junction to case, both legs conducting	— R _{thJC}		-	-	1.75	к/w	
Thermal resistance, junction to ambient	R _{thJA}	R _{thJA} Typical socket mount		-	80		
Weight			-	2	-	g	
weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Marking device		Case style D ² PAK (TO-263AB)		HFA16	TA60CS	•	

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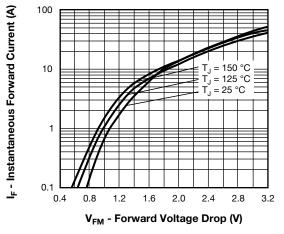


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current (Per Leg)

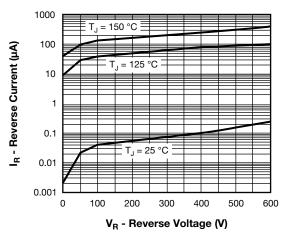


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Leg)

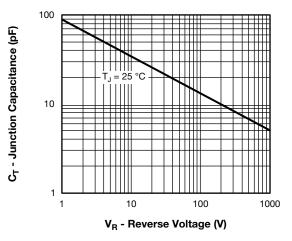
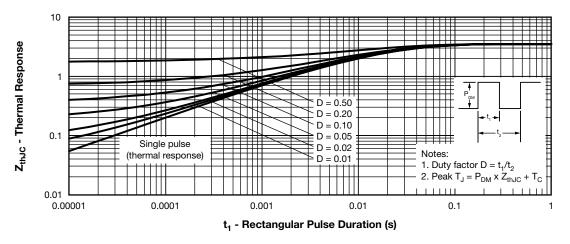
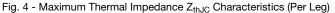


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)





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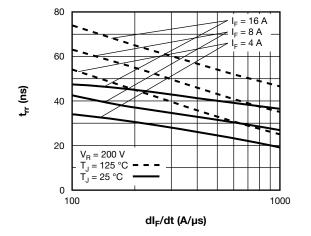


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

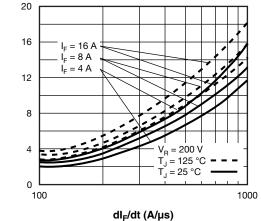


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg

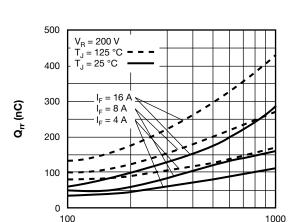




Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

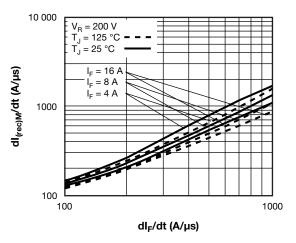


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt (Per Leg)

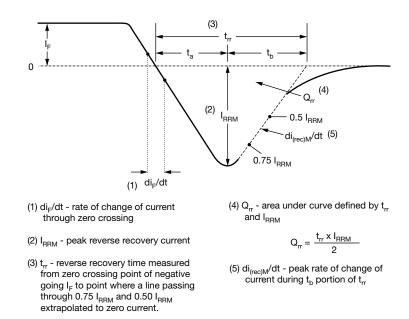


Fig. 9 - Reverse Recovery Waveform and Definitions

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I_{rr} (A)

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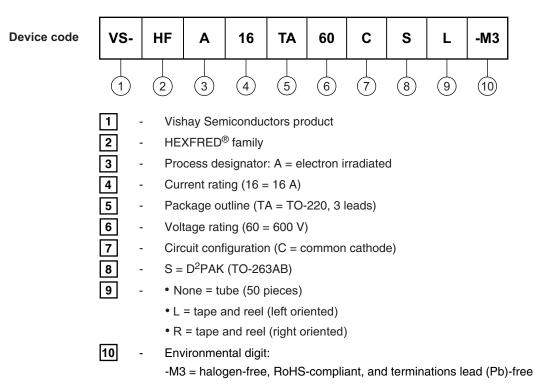
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ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)						
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION				
VS-HFA16TA60CS-M3	50	Antistatic plastic tube				
VS-HFA16TA60CSR-M3	800	13" diameter reel				
VS-HFA16TA60CSL-M3	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96164				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				
SPICE model	www.vishay.com/doc?96596				

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D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	-	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010	BSC	
L4	4.78	5.28	0.188	0.208	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

Revision: 13-Jul-17

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Document Number: 96164

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